



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-89 Plastic-Encapsulate Transistors

KTA1663

TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 0.5 W ($T_{amb}=25^{\circ}C$)

Collector current

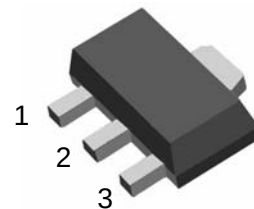
I_{CM} : -1.5 A

Collector-base voltage

$V_{(BR)CBO}$: -35 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



SOT-89

1. BASE

2. COLLECTOR (HEAT SINK)

3. EMITTER

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-1mA, I_E=0$	-35		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-30		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1mA, I_C=0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB}=-30V, I_E=0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$		-0.1	μA
DC current gain	H_{FE}	$V_{CE}=-2V, I_C=-500mA$	100	320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-1.5A, I_B=-30mA$		-2.0	V
Base-Emitter saturation voltage	V_{BE}	$V_{CE}=-2V, I_C=500mA$		-1.0	
Transition frequency	f_T	$V_{CE}=-5V, I_C=-50mA$	80		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		50	pF

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	100-200	160-320
Marking	HO	HY